# **Supporting Information**

# Surface Termination and Strain-Induced Modulation of Structure and Electronic Properties in 2D Perovskites (Cs<sub>2</sub>BCl<sub>4</sub> & CsB<sub>2</sub>Cl<sub>5</sub>, B=Pb,Sn): A first-principles study $^{\dagger}$

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## **Structure and Lattice dynamics**

Table 1 summarizes the structural parameters for 2D perovskites calculated in the present work.

Table 1 :	Comparison	of strue	ctural parameters	of 2	D monolayer	perovskites
Formula unit	Lattice	constant	Thickness (Å)	Rumpling (Å)		Bandgap (eV)
	(Å)					
Cs <sub>2</sub> PbCl <sub>4</sub>	5.65		5.77	0.40		1.72
CsPb <sub>2</sub> Cl <sub>5</sub>	5.68		5.02	0.23		1.70
$Cs_2SnCl_4$	5.56		5.67	0.36		1.34
CsSn <sub>2</sub> Cl <sub>5</sub>	5.57		4.91	0.23		1.83

The cubic phase of perovskite compounds is the most commonly theoretically studied phase, and typically shows many phonon instabilities. The rich structural phases of perovskite-type compounds can trace back to the phonon instability of highly symmetric cubic structure. The phonon dispersions studied here share some of these instabilities at  $\Gamma$ , M and X points, which suggests a rich underlying phase diagram for these 2D systems as well. The exploration of each of the phases stemming from the instabilities, which show ferroelectric, anti-ferrodistortive instabilities.



Fig. S1 Phonon dispersion along the high symmetry path  $\Gamma \rightarrow M \rightarrow X$  for unstrained 2D perovskites monolayer (a) Cs<sub>2</sub>PbCl<sub>4</sub> (b) Cs<sub>2</sub>SnCl<sub>4</sub> (c) CsPb<sub>2</sub>Cl<sub>5</sub> and (d) CsSn<sub>2</sub>Cl<sub>5</sub>.

#### Thermodynamic analysis

**Surface energy,**  $E_{surf}$  and Phase Diagram The relative stability of different surface terminations can be examined from their surface energies and phase diagrams considering varied chemical potential conditions. The surface energy,  $E_{surf}$  of CsCl and BCl<sub>2</sub> (B = Pb or Sn) terminated surfaces can be computed from their dependence on the chemical potential,  $\mu_i$  of elements as:

$$E_{surf}^{x} = \frac{1}{2S} (E_{slab}^{x} - N_{Cs}\mu_{Cs} - N_{B}\mu_{B} - N_{Cl}\mu_{Cl})$$
(1)

where  $E_{surf}^{x}$  (eV) is the total energy of slab X from the DFT calculation.  $N_{Cs}$ ,  $N_B$  and  $N_X$  are the number of atoms (Cs, B, and Cl) in the slab;  $\mu_{Cs}$ ,  $\mu_B$  and  $\mu_{Cl}$  are their chemical potentials; S is the area of the symmetrical surface. The prevention conditions of bulk element (Cs, B = Pb or Sn, and Cl<sub>2</sub>) formations on the surface corresponds to

$$\Delta\mu_{Cs} < 0; \Delta\mu_B < 0; \Delta\mu_{Cl} < 0 \tag{2}$$

where,  $\Delta \mu_i$  is the relative chemical potential. We define relative chemical potential  $\Delta \mu_i$  as

$$\Delta \mu_i = \mu_i - E_i \tag{3}$$

where,  $\mu_i$  is the elemental chemical potential and  $E_i$  (eV per atom) is the total energy of the element phase . Similarly, the condition to prevent binary compound (CsCl and BCl<sub>2</sub>) formation corresponds to:

$$\Delta\mu_{Cs} + \Delta\mu_{Cl} < E_f(CsCl) \tag{4}$$

$$\Delta \mu_B + 2\Delta \mu_{Cl} < E_f(BCl_2) \tag{5}$$

Assuming that the surface is in equilibrium with bulk, we can write

$$\Delta\mu_{Cs} + \Delta\mu_B + 3\Delta\mu_{Cl} = E_f(CsBCl_3) \tag{6}$$

where  $E_f(CsBCl_3)$  is the formation energy of bulk CsPbCl<sub>3</sub>, i.e.,  $E_f(CsBCl_3) = E_{CsPbCl_3} - E_{Cs} - E_B - 3E_{Cl}$ .

We defined the formation energy,  $E_f$  with respect to the elemental substances as:

$$E_f(Cs_iB_jCl_k) = E_{Cs_iB_jCl_k} - iE_{Cs} - jE_B - kE_{Cl}$$

$$\tag{7}$$

where,  $E_{Cs_iB_jCl_k}$  is the total energy of bulk  $Cs_iB_jCl_k$  and  $E_{Cs}$ ,  $E_B$ ,  $E_{Cl}$  are the energies (eV per atom) of elemental substances, i.e., Cs metal, B metal and Cl<sub>2</sub> gas molecule. i, j and k are the number of Cs, B and Cl atoms in the bulk  $Cs_iB_jCl_k$ , respectively.

On using equation (3) and (6),  $E_{surf}$  can be rewritten as :

$$E_{surf}^{x} = \lambda^{x} - \frac{1}{2S} [(N_{Cs} - N_{B})\Delta\mu_{Cs} + (N_{Cl} - 3N_{B})\Delta\mu_{Cl}]$$

$$[F_{x}^{x} = -N_{Dl}E_{D_{x}}\mu - (N_{Cs} - N_{B})E_{Cs} - (N_{Cl} - 3N_{B})E_{Cl}]$$
(8)

where,  $\lambda^{x} = \frac{1}{2S} [E_{slab}^{x} - N_{Pb} E_{Bulk} - (N_{Cs} - N_{B}) E_{Cs} - (N_{Cl} - 3N_{B}) E_{Cl}].$ 

On solving equation (4), (5) and (6), we obtain boundary condition for CsCl-rich and BCl<sub>2</sub>-rich phases and equating surface energies of CsCl and BCl<sub>2</sub> surfaces gives the equilibrium boundary between CsCl and BCl<sub>2</sub> rich phase of the surface phase diagram.

We find thermodynamically stable bulk CsBCl<sub>3</sub> at the chemical potential region between CsClrich and BCl<sub>2</sub>-rich condition:  $-4.25 \le \Delta \mu_{Cs} + \Delta \mu_{Cl} \le -3.92$  eV for CsPbCl<sub>3</sub>;  $-4.32 \le \Delta \mu_{Cs} + \Delta \mu_{Cl} \le -3.92$ eV for CsSnCl<sub>3</sub>. These conditions define the red lines in Fig. 3(a & b) of main text. Binary phase CsCl (yellow marked area) or PbCl<sub>2</sub>/SnCl<sub>2</sub> (blue and green marked areas) may appear beyond these regions.

#### **Conditions to calculate** $E_{surf}$ **as a function of** $\Delta \mu_{Cl}$

In order to show  $E_{surf}$  as a function of  $\Delta\mu_{Cl}$ , we calculate  $E_{surf}$  at specific chemical potential conditions of Cs. We assume Pb/Sn-rich condition (i.e. Pb/Sn = 0 eV) where Pb/Sn source is in equilibrium with CsPbCl<sub>3</sub>/CsSnCl<sub>3</sub>. Using  $\Delta\mu_{Pb} = 0$  eV and  $\Delta\mu_{Sn} = 0$  eV in equation (7), we obtain  $\Delta\mu_{Cs} + 3\Delta\mu_{Cl} = -7.52$  eV for CsPbCl<sub>3</sub> ( $\Delta\mu_{Cl} + 3\Delta\mu_{Cl} = -7.41$  eV for CsSnCl<sub>3</sub> Combining Sn-rich condition with CsCl-rich and PbCl<sub>2</sub>/SnCl<sub>2</sub>-rich conditions of stable CsPbCl<sub>3</sub>/CsSnCl<sub>3</sub>, we can obtain two typical conditions for Cs:  $\Delta\mu_{Cs} = 2.12$  eV and  $\Delta\mu_{Cs} = 2.61$  eV for CsPbCl<sub>3</sub>. Similarly,  $\Delta\mu_{Cs} = 2.18$  eV and  $\Delta\mu_{Cs} = 2.78$  eV for CsSnCl<sub>3</sub>. The E<sub>surf</sub> as a function of  $\Delta\mu_{Cl}$  are calculated at these conditions (SI Figure 2 (c,d).



Fig. S2 (a) Schematic showing the direction of tensile (hollow arrows) and compression (filled arrows) strains on the 2D perovskites. (b) Formation energy,  $E_{form}$  computed from binary phase energies. Blue squares represent  $Cs_2PbCl_4$ , green squares represent  $Cs_2SnCl_4$ , blue triangles represent  $CsPb_2Cl_5$ , and green triangles represent  $CsSn_2Cl_5$ . (c,d) Surface energies ( $E_{surf}$ ) of  $Cs_2BCl_4$  (solid lines) and  $CsB_2Cl_5$  (dotted lines) (B=Pb, Sn) surfaces as a function of  $\Delta\mu_{Cl}$ . The conditions of stable  $CsPbCl_3$  and  $CsSnCl_3$  are marked by blue and green areas.

#### Formation energy using binary compounds

We further calculate formation energies  $E_{form}$  of Cs<sub>2</sub>BCl<sub>4</sub> and CsB<sub>2</sub>Cl<sub>5</sub> monolayer unit cell with respect to their binaries (see Fig. S2(b)) as:

$$E_{form}(Cs_2BCl_4) = E(Cs_2BCl_4) - 2E(CsCl) - E(BCl_2)$$
(9)

$$E_{form}(CsB_2Cl_5) = E(CsB_2Cl_5) - E(CsCl) - 2E(BCl_2)$$
<sup>(10)</sup>

where  $E_{CsCl}$ ,  $E_{BCl_2}$  are the total energies of CsCl, BCl<sub>2</sub> binary compounds atoms. According to this definition of formation energy, negative values of  $E_{form}$  indicates the energetically stable system.

#### **Cleavage energy**

The cleavage energy  $(E_{cl})$  describing the energy cost of cleaving a bulk into two surfaces can be calculated from the total energies of complementary symmetric unrelaxed slabs as:

$$E_{cl} = \frac{1}{2S} \left( E_{slab}^{CsCl} + E_{slab}^{BCl_2} - N_{bulk} E_{bulk} \right)$$
(11)

where  $N_{bulk}$  is the total number of unit cells of CsBCl<sub>3</sub> in the CsCl and BCl<sub>2</sub> terminated slabs.



**Electronic band structure and DOS/PDOS** 

Fig. S3 Electronic band structure along the high symmetry path  $\Gamma \rightarrow M \rightarrow X$  and total and orbital resolved Density of states for strained and strain-free CsCl terminated 2D perovskites,  $Cs_2PbCl_4$  (left column) and  $Cs_2SnCl_4$  (right column).



Fig. S4 Electronic band structure along the high symmetry path  $\Gamma \rightarrow M \rightarrow X$  and total and orbital resolved Density of states for strained7 and strain-free BCl<sub>2</sub> (B=Pb or Sn) terminated 2D perovskites, CsPb<sub>2</sub>Cl<sub>5</sub> (left column) and (b) CsSn<sub>2</sub>Cl<sub>5</sub> (right column).

## Effect of thickness on structure and electronic properties

To understand the effect of material thickness on transport properties, we model 3D bulk and 2D bilayer of these MHPs (see main text fig 5(a)). The corresponding structural and transport parameters highlighting the impact of material thickness are listed in below Table ?. We note that as the number of layers (N) increases, the lattice constant increases and electronic bandgap decreases.

Material	1/N		a (Å)	Thickness (Å)	Rumpling (Å)	$E_g$ (eV)	$\Delta \mu_h(-2\%)$	$\Delta \mu_e(-2\%)$
Bulk	0	Pb	5.738	—	—	0.98	31	29
		Sn	5.636	_	_	0.67	76	67
Bilayer	0.5	Pb	5.72	10.5488	0.4986	1.55	63	16
		Sn	5.62	10.4928	0.4341	1.18	47	17
Monolayer	1	Pb	5.648	4.9651	0.4018	1.72	79	18
		Sn	5.557	4.9622	0.3565	1.34	49	21

Table 2 :	Comparison	of structural	and ele	ectronic	parameter	evolution	with	thickness	and strain
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Fig. S5 Effective mass, m<sup>\*</sup> variations with strain, along  $M \to \Gamma$  and  $M \to X$  for bilayer (a) 2D Cs<sub>3</sub>Pb<sub>2</sub>Cl<sub>7</sub> and (b) 2D Cs<sub>3</sub>Sn<sub>2</sub>Cl<sub>7</sub>. Hollow and filled markers have been used for holes and electrons, respectively. Direction average mobility variations with biaxial strain for (c) Cs<sub>3</sub>Pb<sub>2</sub>Cl<sub>7</sub> and (d) Cs<sub>3</sub>Sn<sub>2</sub>Cl<sub>7</sub>.



Fig. S6 Effective mass, m<sup>\*</sup> variations with strain, along  $R \to \Gamma$ ,  $R \to X$  and  $R \to M$  for (a) CsPbCl<sub>3</sub> and (b) CsSnCl<sub>3</sub> Bulk. Hollow and filled markers have been used for holes and electrons, respectively. Direction average mobility variations with biaxial strain for (c) CsPbCl<sub>3</sub> and (d) CsSnCl<sub>3</sub>.

# Born effective charges

We estimated the Born effective charges as an indicator of ferroelectricity, and find anomolously large charges on the B atom and the Cl ion, which can further be modulated with strain. Our phonon dispersions are consistent with rich phase diagrams in the material. Born effective charges,  $Z^*_{\alpha\beta}$ , manifest coupling between lattice displacements and electrostatic fields. We note that Z<sup>\*</sup> is anomalously large for the parallel Cl and B atom (see fig S5. a-d). The effective charges on the B atom increase from Pb to Sn, with corresponding decrease in size of B-atom, while the effective charge on the Cl atom increases with B-atom size increase. The effective charges on the B-atom increase linearly with decrease in the lattice parameter, while the Cl-atom charge decreases. These variations could be attributed to electronegativity differences between the B atom and the Cl atom.



Fig. S7 Polarization given Born effective charges, Z\* variation with strain (a) B-atom (B=Pb, Sn), (b) Cl-atom of Cs<sub>2</sub>BCl<sub>4</sub>, (c) B-atom (B=Pb, Sn) (d) Cl-atom of CsB<sub>2</sub>Cl<sub>5</sub>. Blue, green curves correspond to Pb and Sn perovskites, respectively.